

# Technische Information / Technical Information

**eupec**

**Dioden-Modul mit Chopper-IGBT**  
**Diode Module with Chopper-IGBT DD B6U 84 N 12...16 RR**



## Elektrische Eigenschaften / Electrical properties

## Vorläufige Daten Preliminary data

### Höchstzulässige Werte / Maximum rated values

| <b>Netz-Diode / Rectifier diode</b>                                             |                                                                                                     |             |                    |                                              |
|---------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------------|-------------|--------------------|----------------------------------------------|
| Periodische Spitzensperrspannung<br>repetitive peak reverse voltage             | $T_{vj} = -40^{\circ}\text{C} \dots T_{vj\text{ max}}$                                              | $V_{RRM}$   | 1200, 1400<br>1600 | V                                            |
| Durchlaßstrom-Grenzeffektivwert (pro Element)<br>RMS forward current (per chip) |                                                                                                     | $I_{FRMSM}$ | 60                 | A                                            |
| Ausgangsstrom<br>output current                                                 | $T_C = 100^{\circ}\text{C}$<br>$T_C = 84^{\circ}\text{C}$                                           | $I_d$       | 85<br>104          | A<br>A                                       |
| Stoßstrom-Grenzwert<br>surge forward current                                    | $T_{vj} = 25^{\circ}\text{C}, t_p = 10\text{ms}$<br>$T_{vj} = T_{vj\text{ max}}, t_p = 10\text{ms}$ | $I_{FSM}$   | 650<br>550         | A<br>A                                       |
| Grenzlastintegral<br>$I^2t$ -value                                              | $T_{vj} = 25^{\circ}\text{C}, t_p = 10\text{ms}$<br>$T_{vj} = T_{vj\text{ max}}, t_p = 10\text{ms}$ | $I^2t$      | 2100<br>1500       | $\text{A}^2\text{s}$<br>$\text{A}^2\text{s}$ |
| <b>IGBT</b>                                                                     |                                                                                                     |             |                    |                                              |
| Kollektor-Emitter-Sperrspannung<br>collector-emitter voltage                    |                                                                                                     | $V_{CES}$   | 1200               | V                                            |
| Kollektor-Dauergleichstrom<br>DC-collector current                              |                                                                                                     | $I_C$       | 50                 | A                                            |
| Periodischer Kollektor-Spitzenstrom<br>repetitive peak collector current        | $t_p = 1\text{ms}$                                                                                  | $I_{CRM}$   | 100                | A                                            |
| Gesamt-Verlustleistung<br>total power dissipation                               | $T_C = 25^{\circ}\text{C}$                                                                          | $P_{tot}$   | 350                | W                                            |
| Gate-Emitter Spitzenspannung<br>gate-emitter peak voltage                       |                                                                                                     | $V_{GE}$    | $\pm 20$           | V                                            |
| <b>Schnelle Diode / Fast diode</b>                                              |                                                                                                     |             |                    |                                              |
| Dauergleichstrom<br>DC forward current                                          |                                                                                                     | $I_F$       | 25                 | A                                            |
| Periodischer Spitzenstrom<br>repetitive peak forward current                    | $t_p = 1\text{ms}$                                                                                  | $I_{FRM}$   | 50                 | A                                            |
| <b>Modul</b>                                                                    |                                                                                                     |             |                    |                                              |
| Isolations-Prüfspannung<br>insulation test voltage                              | RMS, $f = 50\text{Hz}$ , $t = 1\text{min}$                                                          | $V_{ISOL}$  | 2,5                | kV                                           |

### Charakteristische Werte / Characteristic values

| <b>Netz-Diode / Rectifier diode</b>                                          |                                                                                                                                               |                     | min. | typ.       | max. |            |
|------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------|---------------------|------|------------|------|------------|
| Durchlaßspannung<br>forward voltage                                          | $T_{vj} = T_{vj\text{ max}}, I_F = 100\text{A}$                                                                                               | $V_F$               |      |            | 1,55 | V          |
| Schleusenspannung<br>threshold voltage                                       | $T_{vj} = T_{vj\text{ max}}$                                                                                                                  | $V_{(TO)}$          |      |            | 0,75 | V          |
| Ersatzwiderstand<br>forward slope resistance                                 | $T_{vj} = T_{vj\text{ max}}$                                                                                                                  | $r_T$               |      |            | 5,5  | m $\Omega$ |
| Sperrstrom<br>reverse current                                                | $T_{vj} = T_{vj\text{ max}}, V_R = V_{RRM}$                                                                                                   | $i_R$               |      |            | 5    | mA         |
| <b>IGBT</b>                                                                  |                                                                                                                                               |                     |      |            |      |            |
| Kollektor-Emitter Sättigungsspannung<br>collector-emitter saturation voltage | $T_{vj} = 25^{\circ}\text{C}, I_C = 50\text{A}, V_{GE} = 20\text{V}$<br>$T_{vj} = 125^{\circ}\text{C}, I_C = 50\text{A}, V_{GE} = 20\text{V}$ | $V_{CE\text{ sat}}$ |      | 2,5<br>3,1 | 3,2  | V          |
| Gate-Emitter-Schwellspannung<br>gate-emitter threshold voltage               | $T_{vj} = 25^{\circ}\text{C}, I_C = 2\text{mA}, V_{GE} = V_{CE}$                                                                              | $V_{GE(TO)}$        | 4,5  | 5,5        | 6,5  | V          |

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| IGBT                                                             |                                                                                                                                                                   |           | min. | typ.       | max. |                                  |
|------------------------------------------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------|------|------------|------|----------------------------------|
| Eingangskapazität<br>input capacitance                           | $T_{vj} = 25^{\circ}\text{C}$ , $f_0 = 1\text{MHz}$ ,<br>$V_{CE} = 25\text{V}$ , $V_{GE} = 0\text{V}$                                                             | $C_{ies}$ |      | 3,3        |      | nF                               |
| Kollektor-Emitter Reststrom<br>collector-emitter cut-off current | $T_{vj} = 25^{\circ}\text{C}$ , $V_{CE} = 1200\text{V}$ , $V_{GE} = 0\text{V}$<br>$T_{vj} = 125^{\circ}\text{C}$ , $V_{CE} = 1200\text{V}$ , $V_{GE} = 0\text{V}$ | $i_{CES}$ |      | 0,8<br>4,0 | 1    | mA                               |
| Gate-Emitter Reststrom<br>gate leakage current                   | $T_{vj} = 25^{\circ}\text{C}$ , $V_{CE} = 0\text{V}$ , $V_{GE} = 20\text{V}$                                                                                      | $i_{GES}$ |      |            | 500  | nA                               |
| Emitter-Gate Reststrom<br>gate-leakage current                   | $T_{vj} = 25^{\circ}\text{C}$ , $V_{CE} = 0\text{V}$ , $V_{EG} = 20\text{V}$                                                                                      | $i_{EGS}$ |      |            | 500  | nA                               |
| <b>Schnelle Diode / Fast diode</b>                               |                                                                                                                                                                   |           |      |            |      |                                  |
| Durchlaßspannung<br>forward voltage                              | $T_{vj} = 25^{\circ}\text{C}$ , $I_F = 25\text{A}$<br>$T_{vj} = 125^{\circ}\text{C}$ , $I_F = 25\text{A}$                                                         | $V_F$     |      | 2,3<br>1,8 | 2,9  | V                                |
| Sperrverzögerungsladung<br>recovered charge                      | $I_{FM} = 25\text{A}$ , $-di/dt = 800\text{A}/\mu\text{s}$ , $V_R = 600\text{V}$<br>$T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$               | $Q_r$     |      | 2,3<br>6,0 |      | $\mu\text{As}$<br>$\mu\text{As}$ |

## Thermische Eigenschaften / Thermal properties

|                                                                     |                                                                                                                                   |                     |                                     |                                                                      |
|---------------------------------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------|---------------------|-------------------------------------|----------------------------------------------------------------------|
| Innerer Wärmewiderstand<br>thermal resistance, junction to case     | Netz-Diode / Rectifier diode, $\Theta = 120^{\circ}\text{rect}$<br>Transistor / Transistor, DC<br>Schnelle Diode / Fast diode, DC | $R_{thJC}$          | max. 1,45<br>max. 0,38<br>max. 1,00 | $^{\circ}\text{C/W}$<br>$^{\circ}\text{C/W}$<br>$^{\circ}\text{C/W}$ |
| Übergangs-Wärmewiderstand<br>thermal resistance, case to heatsink   | Netz-Diode / Rectifier diode<br>Transistor / Transistor<br>Schnelle Diode / Fast diode                                            | $R_{thCK}$          | max. 0,25<br>max. 0,24<br>max. 0,30 | $^{\circ}\text{C/W}$<br>$^{\circ}\text{C/W}$<br>$^{\circ}\text{C/W}$ |
| Höchstzulässige Sperrschichttemperatur<br>max. junction temperature |                                                                                                                                   | $T_{vj\text{ max}}$ | 150                                 | $^{\circ}\text{C}$                                                   |
| Betriebstemperatur<br>operating temperature                         |                                                                                                                                   | $T_{c\text{ op}}$   | - 40...+150                         | $^{\circ}\text{C}$                                                   |
| Lagertemperatur<br>storage temperature                              |                                                                                                                                   | $T_{stg}$           | - 40...+150                         | $^{\circ}\text{C}$                                                   |

## Mechanische Eigenschaften / Mechanical properties

|                                                                 |                                 |    |                         |    |
|-----------------------------------------------------------------|---------------------------------|----|-------------------------|----|
| Gehäuse, siehe Anlage<br>case, see appendix                     |                                 |    | Seite 3<br>page 3       |    |
| Innere Isolation<br>internal insulation                         |                                 |    | $\text{Al}_2\text{O}_3$ |    |
| Anzugsdrehmoment für mechanische Befestigung<br>mounting torque | Toleranz / tolerance $\pm 15\%$ | M1 | 4                       | Nm |
| Gewicht<br>weight                                               |                                 | G  | typ. 185                | g  |
| Kriechstrecke<br>creepage distance                              |                                 |    | 12,5                    | mm |

## Kühlkörper / heatsinks :

Mit dieser technischen Information werden Halbleiterbauelemente spezifiziert, jedoch keine Eigenschaften zugesichert. Sie gilt in Verbindung mit den zugehörigen Technischen Erläuterungen. / This technical information specifies semiconductor devices but promises no characteristics. It is valid in combination with the belonging technical notes.

